

GS3ABF - GS3MBF

SURFACE MOUNT SILICON RECTIFIER DIODES

VOLTAGE RANGE: 50-1000V CURRENT: 3.0 A

Features

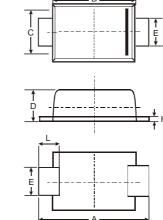
- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Voltage Drop
- Low Power Loss
- Built-in Strain Relief
- Plastic Case Material has UL Flammability Classification Rating 94V-O

Mechanical Data

- Case:SMBF , Molded Plastic
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Marking: Type Number
- Weight: 0.0018 ounces, 0.05grams







SMBF											
Dim	Min	Max	Тур								
Α	5.45	5.55	5.50								
В	4.27	4.33	4.30								
С	3.57	3.63	3.60 1.35								
D	1.32	1.38									
Ε	1.96	2.00	1.98								
Н	0.019	0.021	0.20								
L	0.73	0.77	0.75								
All Dimensions in mm											

Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic		Symbol	GS3ABF	GS3BBF	GS3DBF	GS3GBF	GS3JBF	GS3KBF	GS3MBF	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		Vrrm Vrwm Vr	50	100	200	400	600	800	1000	V
RMS Reverse Voltage		VR(RMS)	35	70	140	280	420	560	700	V
Average Rectified Output Current	lo	3.0							А	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)		IFSM	100							A
Forward Voltage @I _F = 3.0A		VFM	1.20							V
Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 125^{\circ}C$		IRM	5.0 250							μA
Reverse Recovery Time (Note 1)		trr	2.5							μS
Typical Junction Capacitance (Note	Cj	60							pF	
Typical Thermal Resistance (Note 3	R hetaJL	13							°C/W	
Operating and Storage Temperature	Tj, TSTG	-65 to +150							°C	

Note: 1. Measured with I_{F} = 0.5A, I_{R} = 1.0A, I_{rr} = 0.25A,

2. Measured at 1.0 MHz and applied reverse voltage of 4.0 V DC.

3. Mounted on P.C. Board with 8.0mm² land area.



